

500 mW SOD27 Hermetically Sealed Glass Fast Switching Diodes

Absolute Maximum Ratings $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
PD	Power Dissipation	500	mW	
V _{RRM}	Repetitive Peak Reverse Voltage	100	V	
V _R	Continuous Reverse Voltage	100	V	
IF	Continuous Forward Current(see Fig. 2)	200	mA	
I _{FRM}	Repetitive Peak Forward Current	450	mA	
T _{STG}	Storage Temperature Range	-65 to +200	°C	
TJ	Operating Junction Temperature	+200	°C	
IFSM	Non-Repetitive Peak Forward Current Pulse Width : 1.0 µs (see Fig.4) 1.0 ms 1.0 s	4 1 0.5	A A A	

Device mounted on an FR4 printed-circuit board; lead length 10 mm

Specification Features:

- **§** Fast Switching Device (T_{RR} < 4.0 nS)
- § SOD27(DO-35) Package
- § Through-Hole Device Type Mounting
- § Hermetically Sealed Glass
- **§** Compression Bonded Construction
- § All External Surfaces Are Corrosion Resistant And Leads Are Readily Solderable
- **§** RoHS Compliant and Halogen Free
- **§** Solder Hot Dip Tin (Sn) Terminal Finish
- **§** Cathode Indicated By Polarity Band

Electrical Characteristics $T_A = 25^{\circ}C$ unless otherwise noted

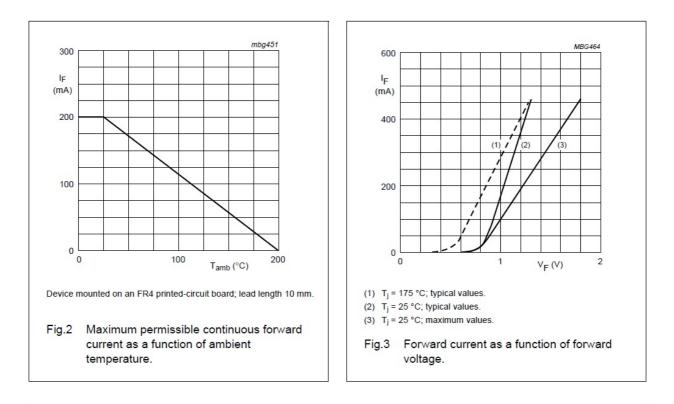
Symbol	Parameter		Test Condition	Limits		
				Min	Max	Unit
V _F	Forward Voltage	PH1N4148	I _F =10mA		1.0	
	(see Fig.3)	PH1N4448	I⊧=5mA	0.62	0.72	V
		PH1N4448	I _F =100mA		1.0	
I _R	Reverse Current	PH1N4148/PH1N4448	V _R =20V		25	nA
	(see Fig.5)	PH1N4148/PH1N4448	V _R =20V,Tj=150℃		50	μA
		PH1N4448	V _R =20V,Tj=100℃		3	μA
С	Capacitance (see Fig.	6)	$V_R=0V$, f=1 M_{HZ}		4	pF
T _{RR}	Reverse Recovery Tin (see Fig.7)	ne	when switched from I _F =10mA to I _R =60mA;R _L =100 Ω measured at I _R =1mA		4	ns
V _{fr}	Forward Recovery Vo	tage(see Fig.8)	when switched from I_F =50mA, T_r =20ns		2.5	V
R _{th(j-tp)}	Thermal Resistance F	orm Junction To Tie-Point	Lead Length 10mm		240	K/W
R _{th(j-a)}	Thermal Resistance F	orm Junction To Ambient	Lead Length 10mm		350	K/W

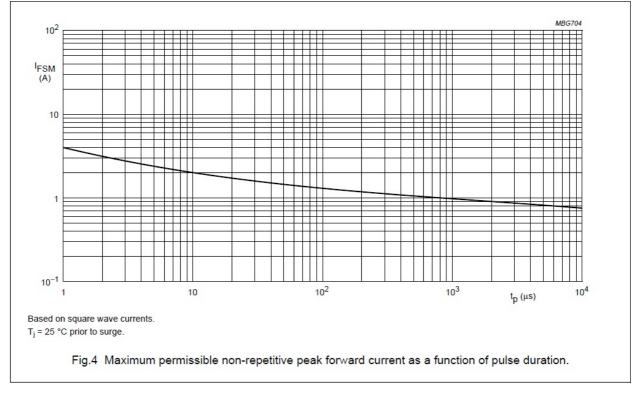


PH1N4148/PH1N4448



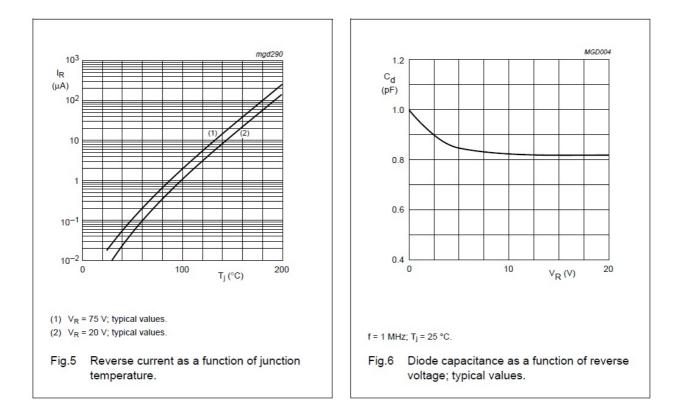
Typical Characteristics





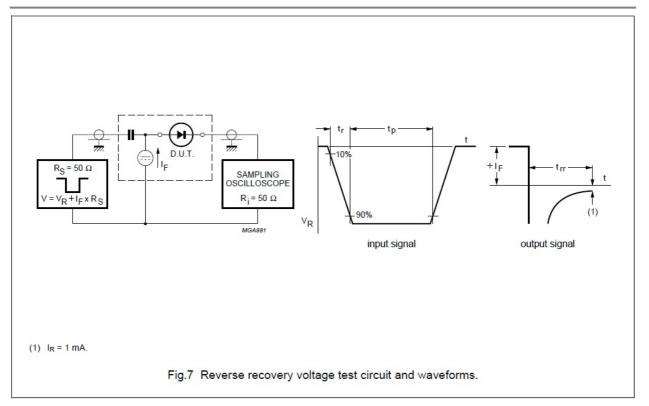


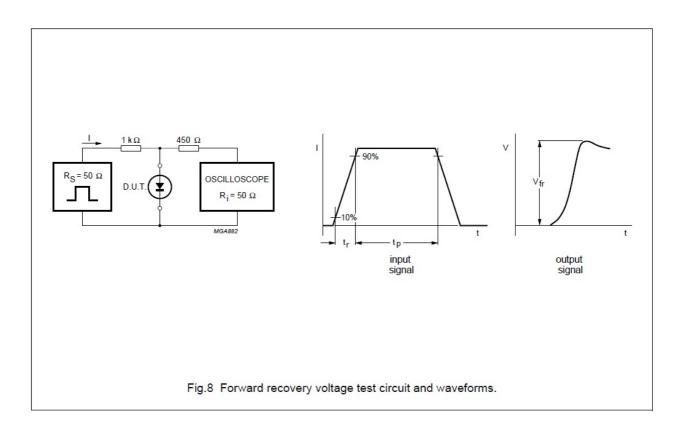
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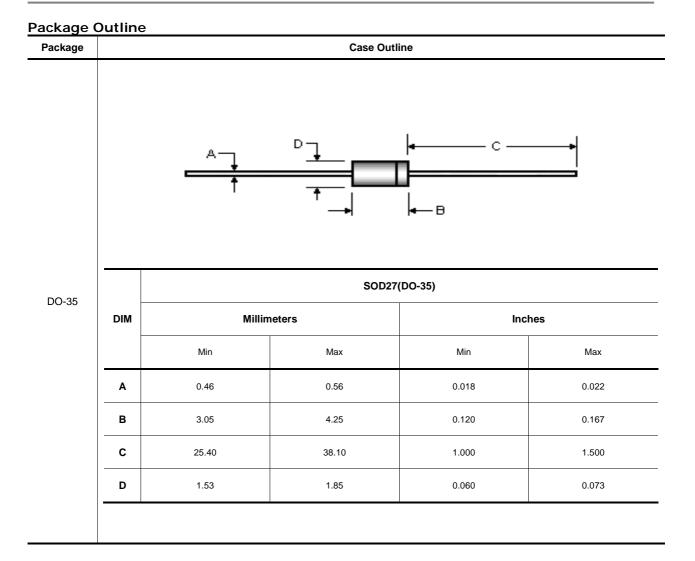


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Notes:

- 1. All dimensions are within JEDEC standard.
- 2. DO35 polarity denoted by cathode band.



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